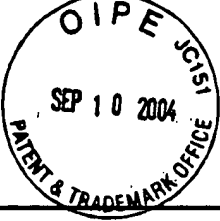


<b>FORM PTO - 1449</b>  <b>INFORMATION DISCLOSURE STATEMENT</b>  				<b>ATTY DOCKET NO.:</b> ASC-049C1  <b>APPLICANT:</b> Fitzgerald  <b>SERIAL NO.:</b> 10/774,890  <b>FILING DATE:</b> February 9, 2004  <b>EXAMINER:</b> Tran, Mai Huong C.  <b>GROUP:</b> 2818			
<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
AK	A1	2001/0003364	06/14/2001	Sugawara <i>et al.</i>			
	A2	2002/0024395	02/28/2002	Akatsuka <i>et al.</i>			
	A3	2002/0043660	04/18/2002	Yamazaki <i>et al.</i>			
	A4	2002/0084000	07/04/2002	Fitzgerald			
	A5	2002/0096717	07/25/2002	Chu <i>et al.</i>			
	A6	2002/0100942	08/01/2002	Fitzgerald <i>et al.</i>			
	A7	2002/0123167	09/05/2002	Fitzgerald			
	A8	2002/0123183	09/05/2002	Fitzgerald			
	A9	2002/0125471	09/12/2002	Fitzgerald <i>et al.</i>			
	A10	2002/0168864	11/14/2002	Cheng <i>et al.</i>			
	A11	2003/0003679	01/02/2003	Doyle <i>et al.</i>			
	A12	2003/0013323	01/16/2003	Hammond <i>et al.</i>			
	A13	2003/0034529	02/20/2003	Fitzgerald <i>et al.</i>			
	A14	2003/0057439	03/27/2003	Fitzgerald			
	A15	2003/0102498	06/05/2003	Braithwaite <i>et al.</i>			
	A16	2003/0199126	10/23/2003	Chu <i>et al.</i>			
	A17	2003/0203600	10/30/2003	Chu <i>et al.</i>			
	A18	2003/0215990	11/20/2003	Fitzgerald <i>et al.</i>			
	A19	2003/0218189	11/27/2003	Christiansen			
	A20	2003/0227057	12/01/2003	Lochtefeld <i>et al.</i>			
	A21	2004/0005740	01/01/2004	Lochtefeld <i>et al.</i>			
	A22	2004/0014304	01/22/2004	Bhattacharyya			
✓	A23	2004/0031979	02/19/2004	Lochtefeld		06/06/2003	
<b>EXAMINER</b> <i>M. Huong C. Tran</i>				<b>DATE CONSIDERED</b> <i>09/22/04</i>			

<b>FORM PTO - 1449</b>				<b>ATTY DOCKET NO.: ASC-049C1</b>			
<b>INFORMATION DISCLOSURE STATEMENT</b>				<b>APPLICANT: Fitzgerald</b>			
				<b>SERIAL NO.: 10/774,890</b>			
				<b>FILING DATE: February 9, 2004</b>			
				<b>EXAMINER: Tran, Mai Huong C.</b>			
				<b>GROUP: 2818</b>			
<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
426	A24	2004/0041210	03/04/2004	Mouli			09/02/2003
	A25	2004/0075149	04/22/2004	Fitzgerald <i>et al.</i>			07/23/2003
	A26	4,010,045	03/01/1977	Ruehrwein			
	A27	4,710,788	12/01/1987	Dambkes <i>et al.</i>			
	A28	4,987,462	01/22/1991	Kim <i>et al.</i>			
	A29	4,990,979	02/05/1991	Otto			
	A30	4,997,776	03/05/1991	Haramé <i>et al.</i>			
	A31	5,013,681	05/07/1991	Godbey <i>et al.</i>			
	A32	5,155,571	10/13/1992	Wang <i>et al.</i>			
	A33	5,166,084	11/24/1992	Pfiester			
	A34	5,177,583	01/05/1993	Endo <i>et al.</i>			
	A35	5,202,284	04/13/1993	Kamins <i>et al.</i>			
	A36	5,207,864	05/04/1993	Bhat <i>et al.</i>			
	A37	5,208,182	05/04/1993	Narayan <i>et al.</i>			
	A38	5,212,110	05/18/1993	Pfiester <i>et al.</i>			
	A39	5,221,413	06/22/1993	Brasen <i>et al.</i>			
	A40	5,240,876	08/34/1993	Gaul <i>et al.</i>			
	A41	5,241,197	08/31/1993	Murakami <i>et al.</i>			
	A42	5,250,445	10/05/1993	Bean <i>et al.</i>			
	A43	5,285,086	02/08/1994	Fitzgerald			
	A44	5,291,439	03/01/1994	Kauffmann <i>et al.</i>			
	A45	5,298,452	03/29/1994	Meyerson			
✓	A46	5,310,451	05/10/1994	Tejwani <i>et al.</i>			
<b>EXAMINER</b> <i>Murakami</i>				<b>DATE CONSIDERED</b> <i>09/22/04</i>			

<b>FORM PTO - 1449</b>  <b>INFORMATION DISCLOSURE STATEMENT</b>				<b>ATTY DOCKET NO.: ASC-049C1</b>  <b>APPLICANT: Fitzgerald</b>  <b>SERIAL NO.: 10/774,890</b>  <b>FILING DATE: February 9, 2004</b>  <b>EXAMINER: Tran, Mai Huong C.</b>  <b>GROUP: 2818</b>			
<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
MH	A47	05/31/1994	Meyerson				
	A48	09/13/1994	Gruppen-Shemansky <i>et al.</i>				
	A49	12/20/1994	Bruel				
	A50	03/21/1995	Ohuri				
	A51	05/09/1995	Godbey				
	A52	06/13/1995	Takasaki				
	A53	06/20/1995	Selvakumar <i>et al.</i>				
	A54	06/20/1995	Mohammad				
	A55	08/15/1995	Brasen <i>et al.</i>				
	A56	10/24/1995	Ek <i>et al.</i>				
	A57	10/24/1995	Burghartz <i>et al.</i>				
	A58	10/31/1995	Dennard <i>et al.</i>				
	A59	12/19/1995	Naruse				
	A60	12/26/1995	Baca <i>et al.</i>				
	A61	01/16/1996	Kitahara <i>et al.</i>				
	A62	06/04/1996	Mohammad				
	A63	06/04/1996	Nakagawa <i>et al.</i>				
	A64	07/09/1996	Ismail <i>et al.</i>				
	A65	07/16/1996	Kondo <i>et al.</i>				
	A66	07/30/1996	Dennard <i>et al.</i>				
	A67	11/05/1996	Shimizu <i>et al.</i>				
	A68	01/21/1997	Tomioka <i>et al.</i>				
✓	A69	04/01/1997	Bertin <i>et al.</i>				
<b>EXAMINER</b> <i>[Signature]</i>				<b>DATE CONSIDERED</b> 438 09/22/04			

<b>FORM PTO - 1449</b>  <b>INFORMATION DISCLOSURE STATEMENT</b>				<b>ATTY DOCKET NO.: ASC-049C1</b>  <b>APPLICANT: Fitzgerald</b>  <b>SERIAL NO.: 10/774,890</b>  <b>FILING DATE: February 9, 2004</b>  <b>EXAMINER: Tran, Mai Huong C.</b>  <b>GROUP: 2818</b>			
<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
	A70	5,630,905	05/20/1997	Lynch <i>et al.</i>			
	A71	5,659,187	08/19/1997	Legoues <i>et al.</i>			
	A72	5,683,934	11/04/1997	Candelaria			
	A73	5,698,869	12/16/1997	Yoshimi <i>et al.</i>			
	A74	5,714,777	02/03/1998	Ismail <i>et al.</i>			
	A75	5,728,623	03/17/1998	Mori			
	A76	5,739,567	04/14/1998	Wong			
	A77	5,759,898	06/02/1998	Ek <i>et al.</i>			
	A78	5,777,347	07/07/1998	Bartelink			
	A79	5,786,612	07/28/1998	Otani <i>et al.</i>			
	A80	5,786,614	07/28/1998	Chuang <i>et al.</i>			
	A81	5,792,679	08/11/1998	Nakato			
	A82	5,808,344	09/15/1998	Ismail <i>et al.</i>			
	A83	5,847,419	12/08/1998	Imai <i>et al.</i>			
	A84	5,877,070	03/02/1999	Goesele <i>et al.</i>			
	A85	5,891,769	04/06/1999	Liaw <i>et al.</i>			
	A86	5,906,708	05/25/1999	Robinson <i>et al.</i>			
	A87	5,906,951	05/25/1999	Chu <i>et al.</i>			
	A88	5,912,479	06/15/1999	Mori <i>et al.</i>			
	A89	5,943,560	08/24/1999	Chang <i>et al.</i>			
A90	5,963,817	10/05/1999	Chu <i>et al.</i>				
A91	5,966,622	10/12/1999	Levine <i>et al.</i>				
A92	5,998,807	12/07/1999	Lustig <i>et al.</i>				
<b>EXAMINER</b>				<b>DATE CONSIDERED</b> 09/22/04			

<b>FORM PTO - 1449</b>				<b>ATTY DOCKET NO.: ASC-049C1</b>			
<b>INFORMATION DISCLOSURE STATEMENT</b>				<b>APPLICANT: Fitzgerald</b>			
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				<b>FILING DATE: February 9, 2004</b>			
				<b>EXAMINER: Tran, Mai Huong C.</b>			
				<b>GROUP: 2818</b>			
<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>11/10</i>	A93	6,013,134	01/11/2000	Chu <i>et al.</i>			
	A94	6,030,887	02/29/2000	Desai <i>et al.</i>			
	A95	6,030,889	02/29/2000	Aulicino <i>et al.</i>			
	A96	6,033,974	03/07/2000	Henley <i>et al.</i>			
	A97	6,033,995	03/07/2000	Muller			
	A98	6,058,044	05/02/2000	Sugiura <i>et al.</i>			
	A99	6,059,895	05/09/2000	Chu <i>et al.</i>			
	A100	6,074,919	06/13/2000	Gardner <i>et al.</i>			
	A101	6,096,590	08/01/2000	Chan <i>et al.</i>			
	A102	6,103,559	08/15/2000	Gardner <i>et al.</i>			
	A103	6,107,653	08/22/2000	Fitzgerald			
	A104	6,111,267	08/29/2000	Fischer <i>et al.</i>			
	A105	6,117,750	09/12/2000	Bensahel <i>et al.</i>			
	A106	6,130,453	10/10/2000	Mei <i>et al.</i>			
	A107	6,133,799	10/17/2000	Favors <i>et al.</i>			
	A108	6,140,687	10/31/2000	Shimomura <i>et al.</i>			
	A109	6,143,636	11/07/2000	Forbes <i>et al.</i>			
	A110	6,153,495	11/28/2000	Kub <i>et al.</i>			
	A111	6,154,475	11/28/2000	Soref <i>et al.</i>			
	A112	6,160,303	12/12/2000	Fattaruso			
	A113	6,162,688	12/19/2000	Gardner <i>et al.</i>			
	A114	6,184,111	02/06/2001	Henley <i>et al.</i>			
<i>✓</i>	A115	6,191,007	02/20/2001	Matsui <i>et al.</i>			
<b>EXAMINER</b> <i>Mei Johnson</i>				<b>DATE CONSIDERED</b> <i>09/22/04</i>			


<b>FORM PTO - 1449</b>  <b>INFORMATION DISCLOSURE STATEMENT</b>				<b>ATTY DOCKET NO.:</b> ASC-049C1  <b>APPLICANT:</b> Fitzgerald  <b>SERIAL NO.:</b> 10/774,890  <b>FILING DATE:</b> February 9, 2004  <b>EXAMINER:</b> Tran, Mai Huong C.  <b>GROUP:</b> 2818			
<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
<i>uH</i> <div style="border-left: 1px solid black; height: 100%; width: 1px; margin: 0 auto;"></div>	A116	6,191,432	02/20/2001	Sugiyama <i>et al.</i>			
	A117	6,194,722	02/27/2001	Fiorini <i>et al.</i>			
	A118	6,204,529	03/20/2001	Lung <i>et al.</i>			
	A119	6,207,977	03/27/2001	Augusto			
	A120	6,210,988	04/03/2001	Howe <i>et al.</i>			
	A121	6,218,677	04/17/2001	Broekaert			
	A122	6,232,138	05/15/2001	Fitzgerald <i>et al.</i>			
	A123	6,235,567	05/22/2001	Huang			
	A124	6,242,324	06/05/2001	Kub <i>et al.</i>			
	A125	6,249,022	06/19/2001	Lin <i>et al.</i>			
	A126	6,251,755	06/26/2001	Furukawa <i>et al.</i>			
	A127	6,261,929	07/17/2001	Gehrke <i>et al.</i>			
	A128	6,266,278	07/24/2001	Harari <i>et al.</i>			
	A129	6,271,551	08/07/2001	Schmitz <i>et al.</i>			
	A130	6,271,726	08/07/2001	Fransis <i>et al.</i>			
	A131	6,291,321	09/18/2001	Fitzgerald			
	A132	6,313,016	11/06/2001	Kibbel <i>et al.</i>			
	A133	6,316,301	11/13/2001	Kant			
A134	6,323,108	11/27/2001	Kub <i>et al.</i>				
A135	6,329,063	12/11/2001	Lo <i>et al.</i>				
A136	6,335,546	01/01/2002	Tsuda <i>et al.</i>				
A137	6,339,232	01/15/2002	Takagi				
<div style="border-left: 1px solid black; height: 100%; width: 1px; margin: 0 auto;"></div>	A138	6,350,993	02/26/2002	Chu <i>et al.</i>			
<b>EXAMINER</b> <i>M. Tran</i>				<b>DATE CONSIDERED</b> <i>09/22/04</i>			

<b>FORM PTO - 1449</b>  <b>INFORMATION DISCLOSURE STATEMENT</b>				ATTY DOCKET NO.: ASC-049C1  APPLICANT: Fitzgerald  SERIAL NO.: 10/774,890  FILING DATE: February 9, 2004  EXAMINER: Tran, Mai Huong C.  GROUP: 2818			
<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
UH	A139	03/05/2002	Usenko				
	A140	04/09/2002	Nishinaga				
	A141	04/16/2002	Thornton <i>et al.</i>				
	A142	04/16/2002	Hattori <i>et al.</i>				
	A143	06/04/2002	Kubo <i>et al.</i>				
	A144	06/11/2002	Brunner <i>et al.</i>				
	A145	06/18/2002	Tezuka				
	A146	07/16/2002	Akatsuka <i>et al.</i>				
	A147	07/30/2002	Chu <i>et al.</i>				
	A148	08/06/2002	Rim				
	A149	02/18/2003	Wu <i>et al.</i>				
	A150	02/25/2003	Canaperi <i>et al.</i>				
	A151	04/29/2003	Fitzgerald				
	A152	06/03/2003	Cheng <i>et al.</i>				
	A153	06/24/2003	Fitzgerald <i>et al.</i>				
	A154	07/15/2003	Fitzgerald				
	A155	07/15/2003	Fitzgerald				
	A156	08/05/2003	Fitzgerald				
	A157	08/05/2003	Rim				
	A158	11/11/2003	Fitzgerald				
	A159	11/18/2003	Fitzgerald <i>et al.</i>				
	A160	01/13/2004	Fitzgerald				
✓	A161	03/09/2004	Fitzgerald			03/18/2003	
EXAMINER <i>M. Tran</i>				DATE CONSIDERED <i>09/22/04</i>			

<b>FORM PTO - 1449</b>				<b>ATTY DOCKET NO.: ASC-049C1</b>					
<b>INFORMATION DISCLOSURE STATEMENT</b>				<b>APPLICANT: Fitzgerald</b>					
				<b>SERIAL NO.: 10/774,890</b>					
				<b>FILING DATE: February 9, 2004</b>					
				<b>EXAMINER: Tran, Mai Huong C.</b>					
				<b>GROUP: 2818</b>					
<b>U.S. PATENT DOCUMENTS</b>									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
MH	A162	6,703,688	03/09/2004	Fitzgerald			07/16/2001		
	A163	6,709,903	03/23/2004	Christiansen			04/30/2003		
	A164	6,713,326	03/30/2004	Cheng <i>et al.</i>			03/04/2003		
	A165	6,723,661	04/20/2004	Fitzgerald			07/16/2001		
	A166	6,724,008	04/20/2004	Fitzgerald			07/16/2001		
	A167	6,730,551	05/04/2004	Lee <i>et al.</i>			08/02/2002		
	A168	6,737,670	05/18/2004	Cheng <i>et al.</i>			03/07/2003		
	A169	6,750,130	06/15/2004	Fitzgerald			01/07/2001		
<b>FOREIGN PATENT DOCUMENTS</b>									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
MH	B1	41 01 167	07/23/1992	DE				N	Y (Abstract only)
	B2	0 514 018	11/19/1992	EP				N	Y
	B3	0 587 520	03/16/1994	EP				N	Y
	B4	0 683 522	11/22/1995	EP				N	Y
	B5	0 828 296	03/11/1998	EP				N	Y
	B6	0 829 908	03/18/1998	EP				N	Y
	B7	0 838 858	04/29/1998	EP				N	Y (Abstract only)
	B8	1 020 900	07/19/2000	EP				N	Y
	B9	1 174 928	01/23/2002	EP				N	Y
	B10	2 701 599	09/01/1993	FR				Y	Y
	B11	2 342 777	04/19/2000	GB				N	Y
	B12	61/141116	06/28/1986	JP				N	Y (Abstract only)
	B13	2/210816	08/22/1990	JP				N	Y (Abstract only)
<b>EXAMINER</b> <i>Chuan Kuan</i>				<b>DATE CONSIDERED</b> <i>09/22/04</i>					



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<b>INFORMATION DISCLOSURE STATEMENT</b>				<b>APPLICANT: Fitzgerald</b>					
				<b>SERIAL NO.: 10/774,890</b>					
				<b>FILING DATE: February 9, 2004</b>					
				<b>EXAMINER: Tran, Mai Huong C.</b>					
				<b>GROUP: 2818</b>					
<b>U.S. PATENT DOCUMENTS</b>									
<b>EXAM. INIT.</b>		<b>DOCUMENT NUMBER</b>	<b>DATE</b>	<b>NAME</b>	<b>CLASS</b>	<b>SUB CLASS</b>	<b>FILING DATE IF APPROPRIATE</b>		
<b>FOREIGN PATENT DOCUMENTS</b>									
<b>EXAM. INIT.</b>		<b>DOCUMENT NUMBER</b>	<b>DATE</b>	<b>COUNTRY CODE</b>	<b>CLASS</b>	<b>SUB CLASS</b>	<b>FILING DATE</b>	<b>ABSTRACT ONLY</b>	<b>ENGLISH LANG (Y/N)</b>
11/11	B14	3/036717	02/18/1991	JP				N	Y
	B15	4-307974	10/30/1992	JP				N	Y (Abstract only)
	B16	5-166724	07/23/1993	JP				N	Y (Abstract only)
	B17	6-177046	06/24/1994	JP				N	Y (Abstract only)
	B18	6-244112	09/02/1994	JP				Y	Y
	B19	6-252046	09/09/1994	JP				Y	Y
	B20	7-094420	04/07/1995	JP				N	Y (Abstract only)
	B21	7-106446	04/21/1995	JP				Y	Y
	B22	7-240372	09/12/1995	JP				Y	Y
	B23	10-270685	10/09/1998	JP				N	Y
	B24	11-233744	08/27/1999	JP				N	Y (Abstract only)
	B25	2000-021783	01/21/2000	JP				N	Y
	B26	2000-031491	01/28/2000	JP				Y	Y
	B27	2001-319935	11/16/2001	JP				N	Y
	B28	2002-076334	03/15/2002	JP				N	Y
	B29	2002-164520	06/07/2002	JP				N	Y
	B30	2002-289533	10/04/2002	JP				N	Y
	B31	98/59365	12/30/1998	WO				N	Y
	B32	99/53539	10/21/1999	WO				N	Y
	B33	00/48239	08/17/2000	WO				N	Y
<b>EXAMINER</b> <i>M. Huong C. Tran</i>				<b>DATE CONSIDERED</b> <i>09/22/04</i>					

<b>FORM PTO - 1449</b>  <b>INFORMATION DISCLOSURE STATEMENT</b>				<b>ATTY DOCKET NO.:</b> ASC-049C1  <b>APPLICANT:</b> Fitzgerald  <b>SERIAL NO.:</b> 10/774,890  <b>FILING DATE:</b> February 9, 2004  <b>EXAMINER:</b> Tran, Mai Huong C.  <b>GROUP:</b> 2818						
U.S. PATENT DOCUMENTS										
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE			
FOREIGN PATENT DOCUMENTS										
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)	
UH	B34	00/54338	09/14/2000	WO				N	Y	
	B35	01/22482	03/29/2001	WO				N	Y	
	B36	01/54202	07/26/2001	WO				N	Y	
	B37	01/93338	12/06/2001	WO				N	Y	
	B38	01/99169	12/27/2001	WO				N	Y	
	B39	02/13262	02/14/2002	WO				N	Y	
	B40	02/15244	02/21/2002	WO				N	Y	
	B41	02/27783	04/04/2002	WO				N	Y	
	B42	02/47168	06/13/2002	WO				N	Y	
	B43	02/071488	09/12/2002	WO				N	Y	
	B44	02/071491	09/12/2002	WO				N	Y	
	B45	02/071495	09/12/2002	WO				N	Y	
	B46	02/082514	10/17/2002	WO				N	Y	
	B47	04/006311	01/15/2004	WO				N	Y	
	B48	04/006327	01/15/2004	WO				N	Y	
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ut	C2	Armstrong, "Technology for SiGe Heterostructure-Based CMOS Devices," Ph.D. Thesis, Massachusetts Institute of Technology, Department of Electrical Engineering and Computer Science (June 30, 1999), pp. 1-154.							
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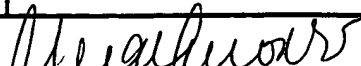
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				EXAMINER: Tran, Mai Huong C.					
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